# **Silicon Controlled Rectifiers**Reverse Blocking Triode Thyristors

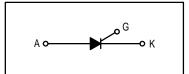
... Annular PNPN devices designed for high volume consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-226AA (TO-92) package which is readily adaptable for use in automatic insertion equipment.

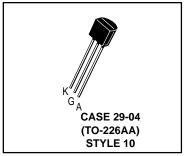
- Sensitive Gate Trigger Current 200 μA Maximum
- Low Reverse and Forward Blocking Current 50  $\mu$ A Maximum,  $T_C$  = 125 $^{\circ}$ C
- Low Holding Current 5 mA Maximum
- · Passivated Surface for Reliability and Uniformity

2N5060 2N5061 2N5062\* 2N5064\*

\*Motorola preferred devices

SCRs 0.8 AMPERES RMS 30 thru 200 VOLTS





## **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit	
*Peak Repetitive Forward and Reverse Blocking Voltage <sup>(1)</sup> (T <sub>J</sub> = 25 to 125°C) (R <sub>GK</sub> = 1000 ohms) 2N5060 2N5061 2N5062 2N5064	VDRM or VRRM	30 60 100 200	Volts	
On-State Current RMS (All Conduction Angles)	IT(RMS)	0.8	Amp	
*Average On-State Current $(T_C = 67^{\circ}C)$ $(T_C = 102^{\circ}C)$	I <sub>T(AV)</sub>	0.51 0.255	Amp	
*Peak Non-repetitive Surge Current, T <sub>A</sub> = 25°C (1/2 cycle, Sine Wave, 60 Hz)	I <sub>TSM</sub>	10	Amps	
Circuit Fusing Considerations (t = 8.3 ms)	I <sup>2</sup> t	0.4	A <sup>2</sup> s	
*Peak Gate Power, T <sub>A</sub> = 25°C	P <sub>GM</sub>	0.1	Watt	
*Average Gate Power, T <sub>A</sub> = 25°C	P <sub>G(AV)</sub>	0.01	Watt	
*Peak Forward Gate Current, T <sub>A</sub> = 25°C (300 µs, 120 PPS)	IFGM	1	Amp	
*Peak Reverse Gate Voltage	<sup>V</sup> RGM	5	Volts	

\*Indicates JEDEC Registered Data.

(cont.)

Preferred devices are Motorola recommended choices for future use and best overall value. REV 1



V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate
voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current
source such that the voltage ratings of the devices are exceeded.

## **MAXIMUM RATINGS** — continued

Rating	Symbol	Value	Unit
*Operating Junction Temperature Range @ Rated V <sub>RRM</sub> and V <sub>DRM</sub>	TJ	-65 to +125	°C
*Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
*Lead Solder Temperature (Lead Length ≥ 1/16" from case, 10 s Max)	_	+230*	°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction to Case <sup>(1)</sup>	$R_{ heta JC}$	75	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C, R<sub>GK</sub> = 1000 $\Omega$ unless otherwise noted.), (2)

Characteristic		Symbol	Min	Тур	Max	Unit
*Peak Repetitive Forward or Reverse Blocking Current (VAK = Rated VDRM or VRRM)	T <sub>C</sub> = 25°C T <sub>C</sub> = 125°C	<sup>I</sup> DRM <sup>, I</sup> RRM	- -	_ _	10 50	μΑ μΑ
*Forward "On" Voltage(3) (I <sub>TM</sub> = 1.2 A peak @ T <sub>A</sub> = 25°C)		Vтм	-	_	1.7	Volts
Gate Trigger Current (Continuous dc) <sup>(4)</sup> *(Anode Voltage = 7 Vdc, R <sub>L</sub> = 100 Ohms)	T <sub>C</sub> = 25°C T <sub>C</sub> = -65°C	<sup>I</sup> GT	- -	_ _	200 350	μА
Gate Trigger Voltage (Continuous dc)  *(Anode Voltage = 7 Vdc, R <sub>L</sub> = 100 Ohms)  (Anode Voltage = Rated V <sub>DRM</sub> , R <sub>L</sub> = 100 Ohms)	$T_{C} = 25^{\circ}C$ $T_{C} = -65^{\circ}C$ $T_{C} = 125^{\circ}C$	V <sub>GT</sub> V <sub>GD</sub>	- - 0.1		0.8 1.2 –	Volts
Holding Current *(Anode Voltage = 7 Vdc, initiating current = 20 mA)	T <sub>C</sub> = 25°C T <sub>C</sub> = -65°C	lн	- -	_ _	5 10	mA
Turn-On Time  Delay Time  Rise Time $(I_{GT} = 1 \text{ mA}, V_D = \text{Rated } V_{DRM},$ Forward Current = 1 A, di/dt = 6 A/ $\mu$ s		<sup>t</sup> d <sup>t</sup> r	_ _	3 0.2	- -	μѕ
Turn-Off Time  (Forward Current = 1 A pulse, Pulse Width = 50 μs, 0.1% Duty Cycle, di/dt = 6 A/μs, dv/dt = 20 V/μs, I <sub>GT</sub> = 1 mA)  2N5060, 2N50 2N5062, 5063,		tq	- -	10 30	_ _ _	μѕ
Forward Voltage Application Rate (Rated V <sub>DRM</sub> , Exponential)		dv/dt	-	30	-	V/μs

<sup>\*</sup>Indicates JEDEC Registered Data.

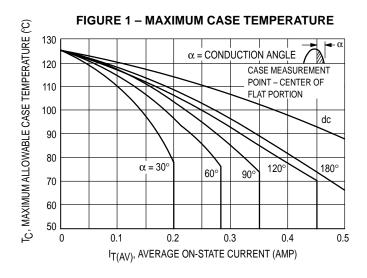
<sup>1.</sup> This measurement is made with the case mounted "flat side down" on a heat sink and held in position by means of a metal clamp over the curved surface.

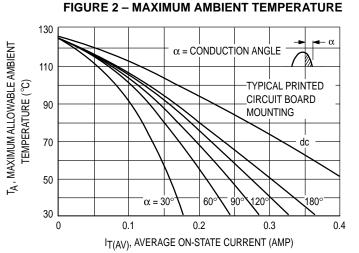
<sup>2.</sup> For electrical characteristics for gate-to-cathode resistance other than 1000 ohms see Motorola Bulletin EB-30.

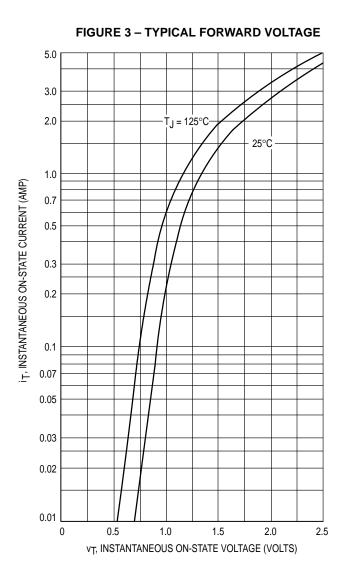
<sup>3.</sup> Forward current applied for 1 ms maximum duration, duty cycle  $\leq$  1%.

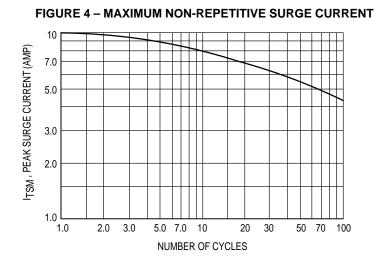
<sup>4.</sup> RGK current is not included in measurement.

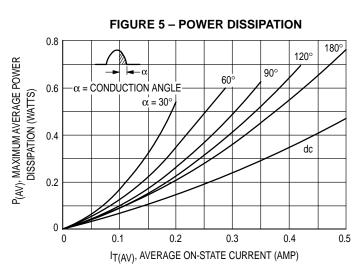
#### **CURRENT DERATING**



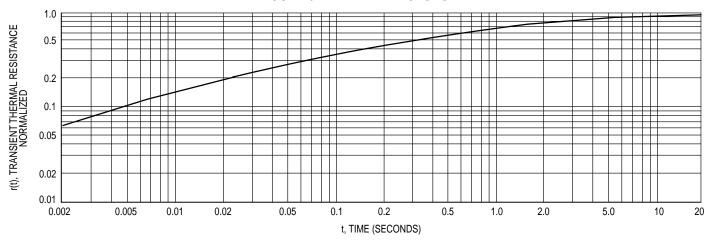








## FIGURE 6 - THERMAL RESPONSE



#### TYPICAL CHARACTERISTICS

FIGURE 7 - GATE TRIGGER VOLTAGE

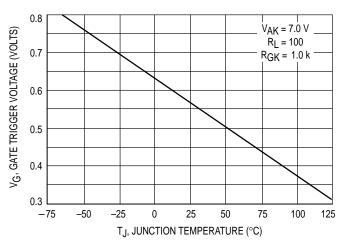
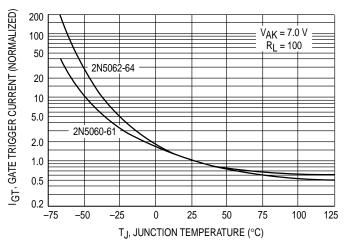
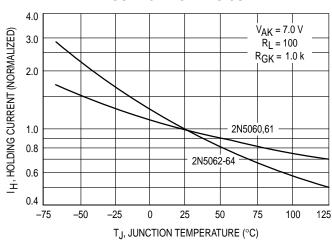


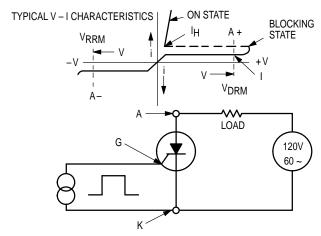
FIGURE 8 - GATE TRIGGER CURRENT



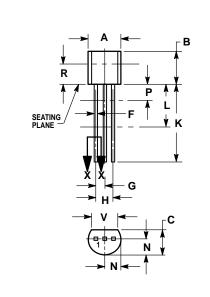
**FIGURE 9 – HOLDING CURRENT** 



## FIGURE 10 - CHARACTERISTICS AND SYMBOLS



# **PACKAGE DIMENSIONS**



STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

  4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION TO APPLY BETWEEN LAND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
Ν	0.080	0.105	2.04	2.66	
Ъ		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

CASE 029-04 (TO-226AA)

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